

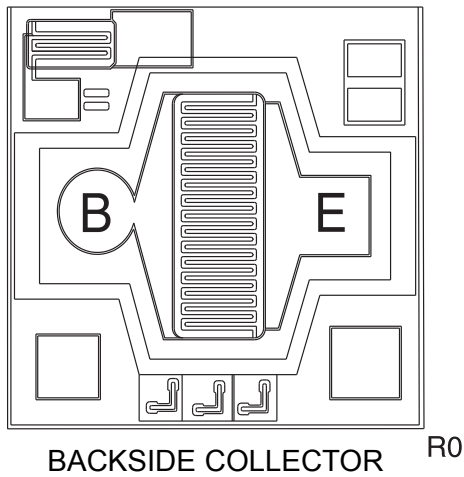
**PROCESS CP616**  
**Small Signal Transistor**  
PNP - Silicon RF Transistor Chip

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	21.7 x 21.7 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 MILS DIAMETER
Emitter Bonding Pad Area	3.5 x 3.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 10,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

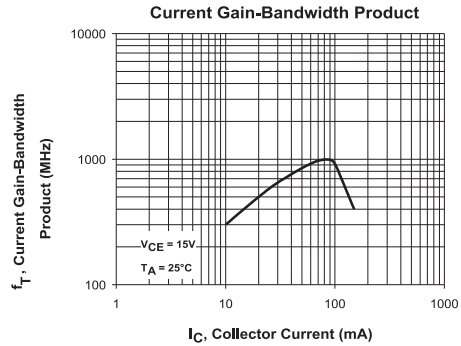
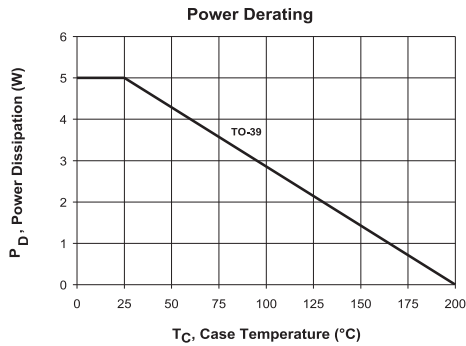
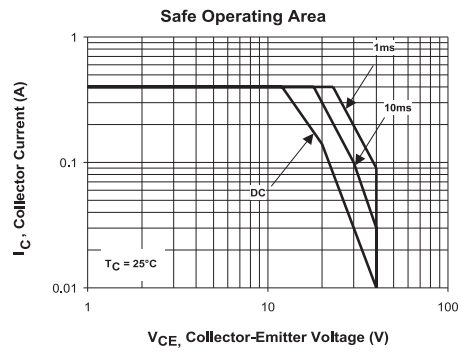
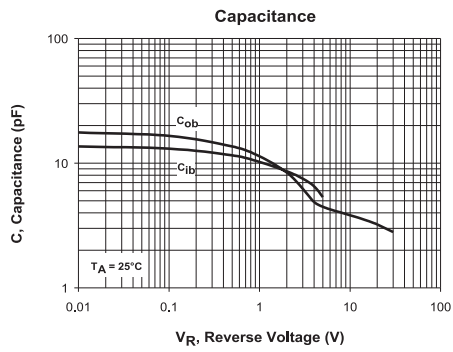
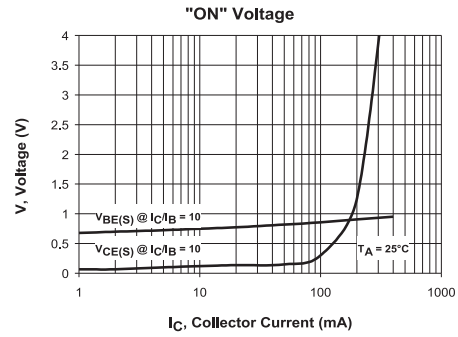
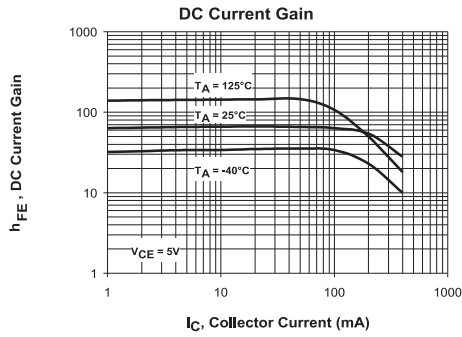
24,790

**PRINCIPAL DEVICE TYPES**

CM5160

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